

SFB/TR16

Precision Compton Polarimetry using a counting silicon microstrip detector

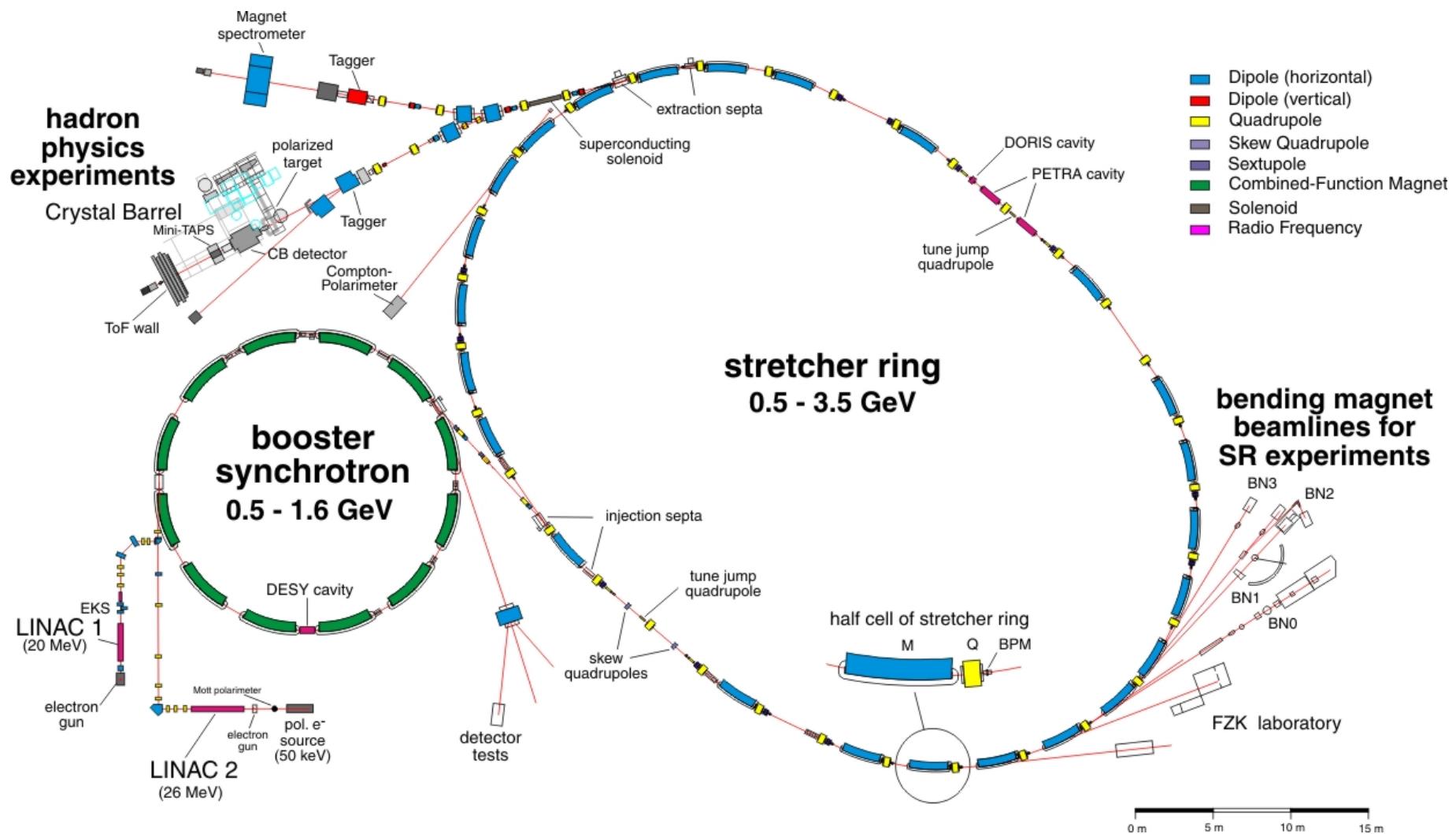
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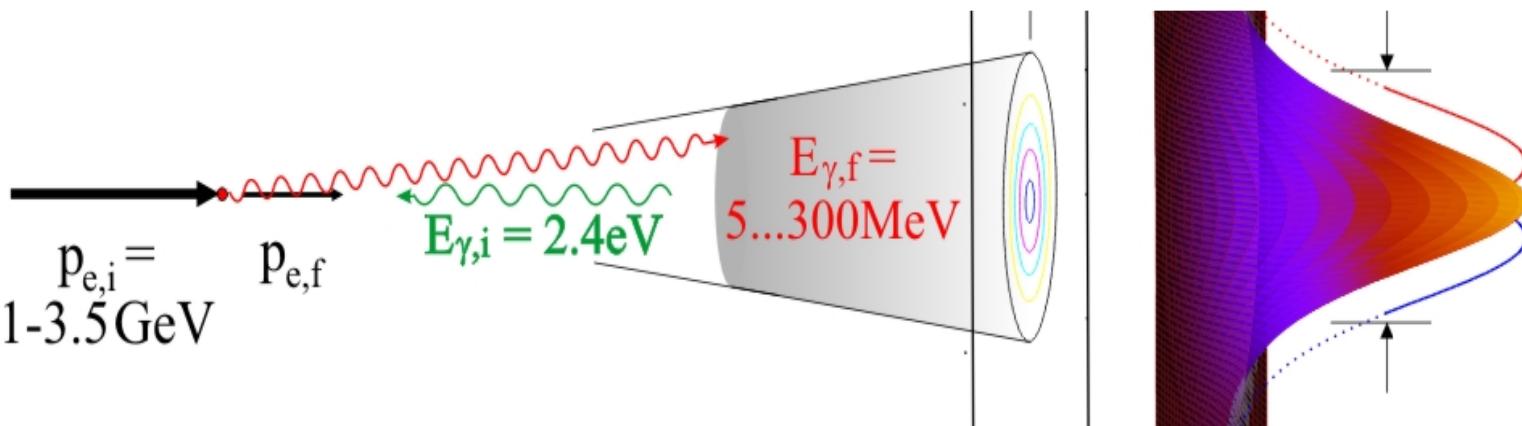
Precision Compton Polarimetry using a counting silicon microstrip detector

- Compton Polarimetry
- Simulations
- Detector Design
- Laser Beam Line
- Other possible beam diagnostics

Overview



Compton Scattering



Differential cross section:

$$\frac{d\sigma}{d\Omega^*}(\vec{S}, \vec{P}) = \Sigma_0 + \Sigma_1(S_1) + \Sigma_2(S_3, \vec{P})$$

Term for the polarized electrons:

transversal

$$\begin{aligned} \Sigma_2(S_3, \vec{P}) &= -S_3 [P_z \cdot C K_f^* \sin \vartheta^* (1 - \cos \vartheta^*) \sin \varphi \\ &\quad - S_3 P_s \cdot C K_f^* (1 - \cos \vartheta^*) (K_f^* + K_i^*) \cos \vartheta^*] \end{aligned}$$

longitudinal

Compton kinematics:

$$K_f^* = \frac{K_i^*}{1 + K_i^* \cdot (1 - \cos \vartheta^*)}$$

spatial asymmetry

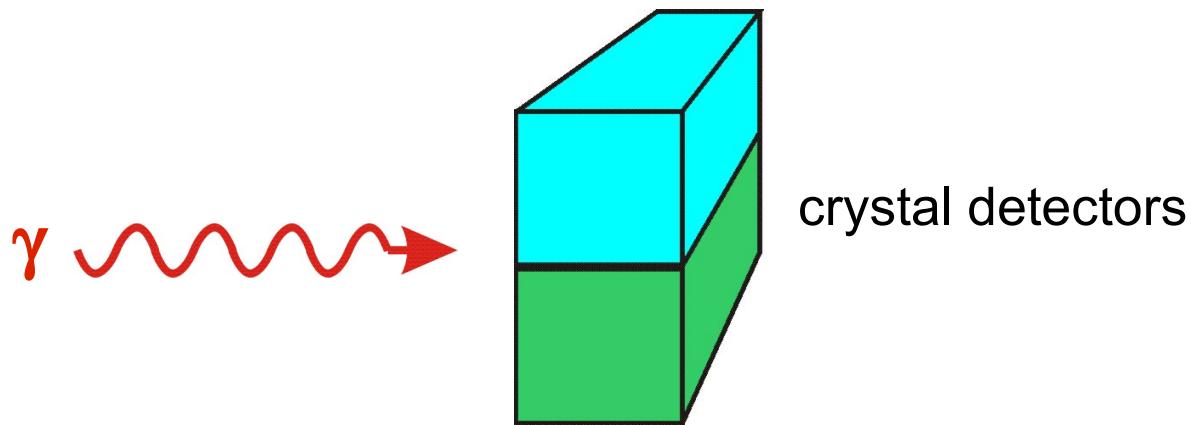
counting rate asymmetry

$$C = \frac{r_e^2}{2} \cdot \left(\frac{K_f^*}{K_i^*} \right)$$

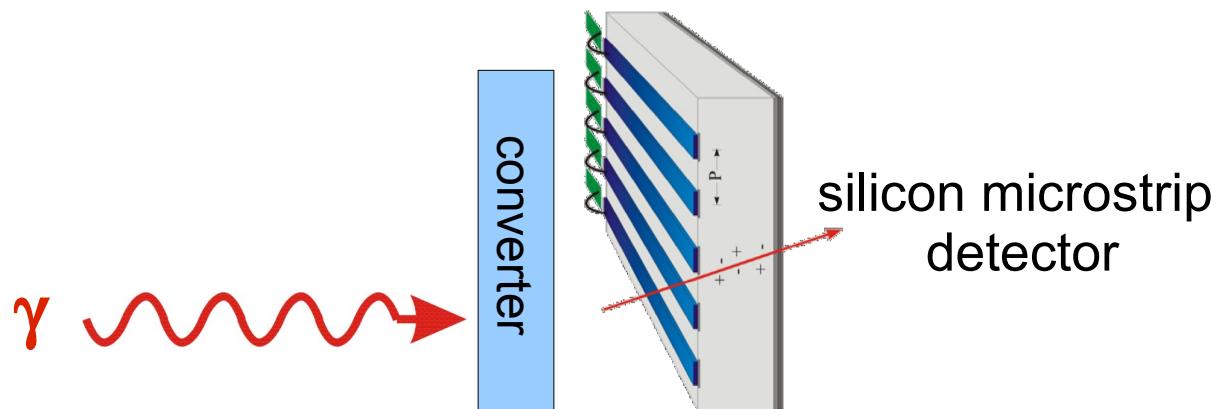
Different types of Compton Polarimeters for transversal polarized electrons

We can measure either:

- integral up down counting rate asymmetry

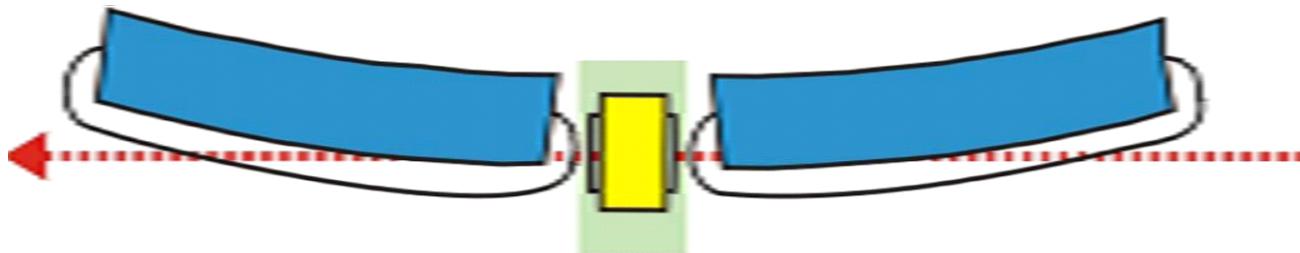


- shift of the center of the spatial distribution

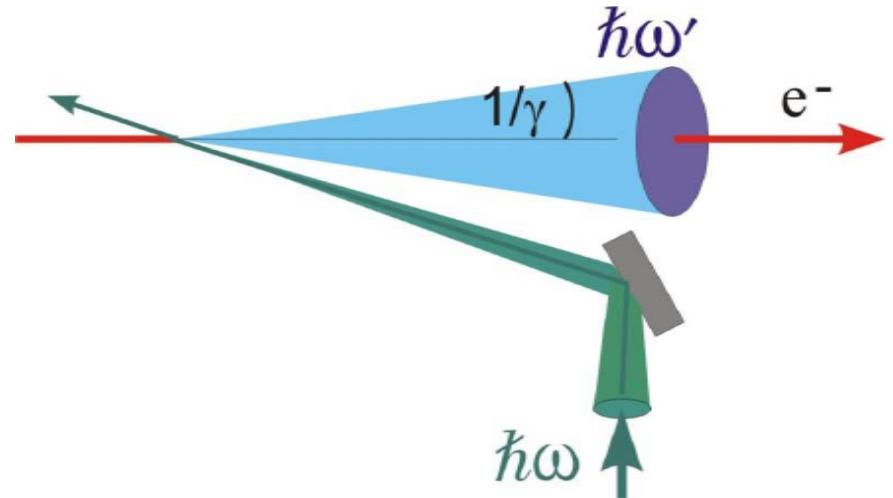


Design Criteria

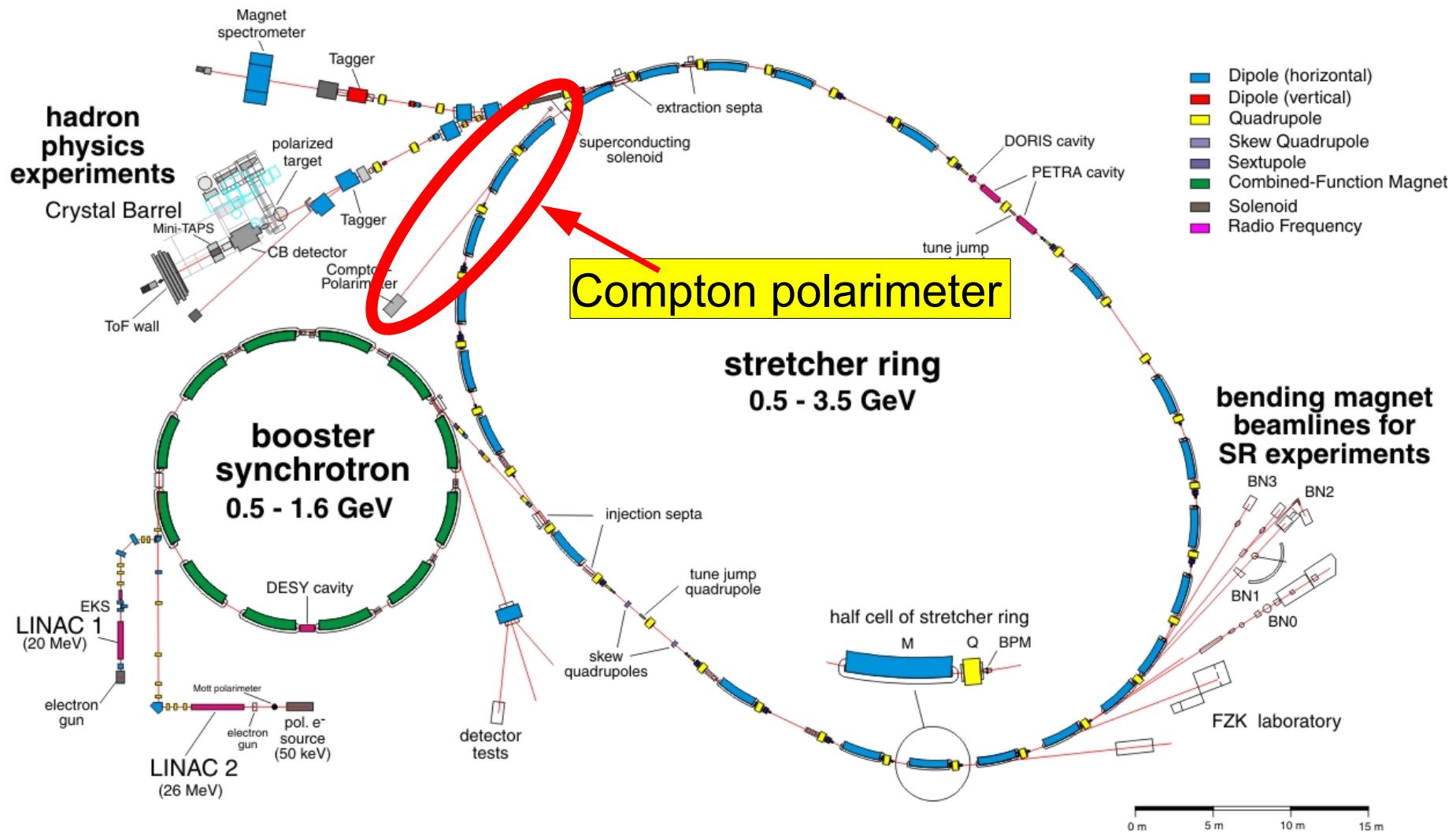
- Electron scattering on restgas causes high energy background
→ **use only a short straight section**



- crossing angle: $\delta \approx 3\text{mrad}$
- interaction region length: 0.7 m
- distance i.r.↔ detector: 15 m



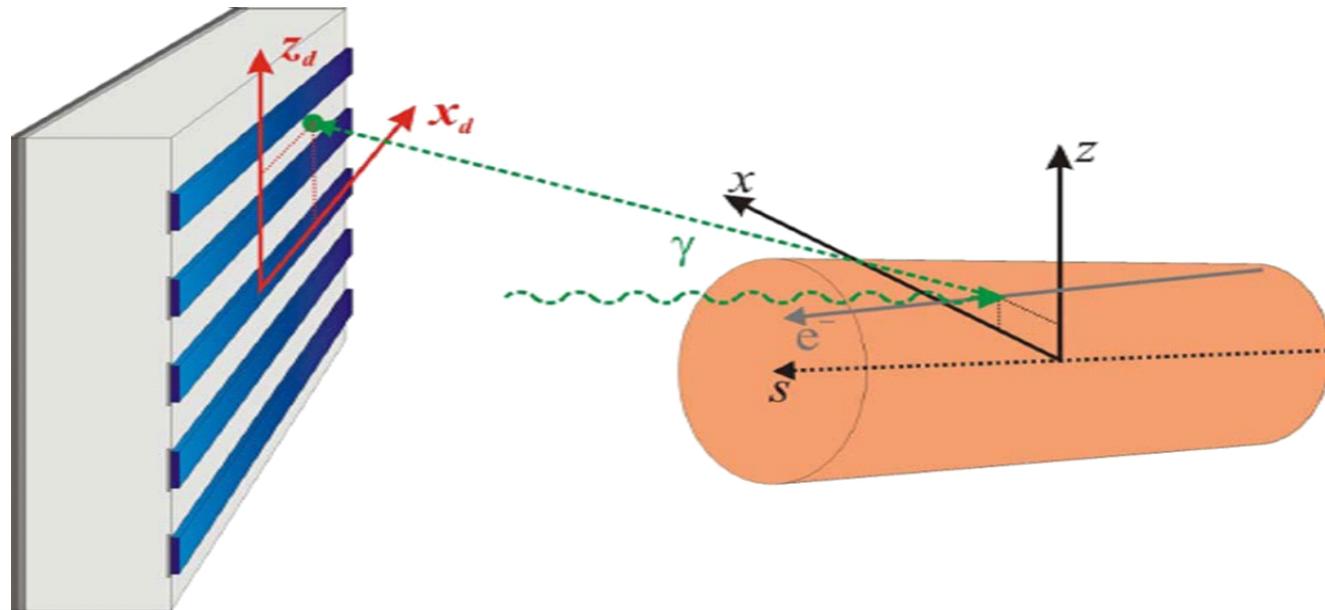
Design Criteria



Simulation of the Compton Process

Numerical integration over the 5 dimensional phase space

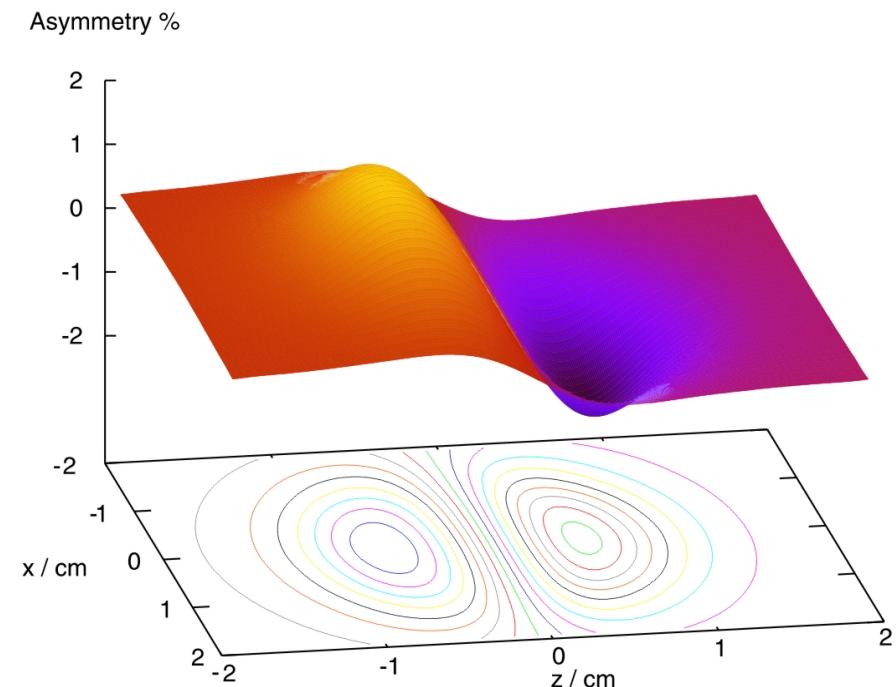
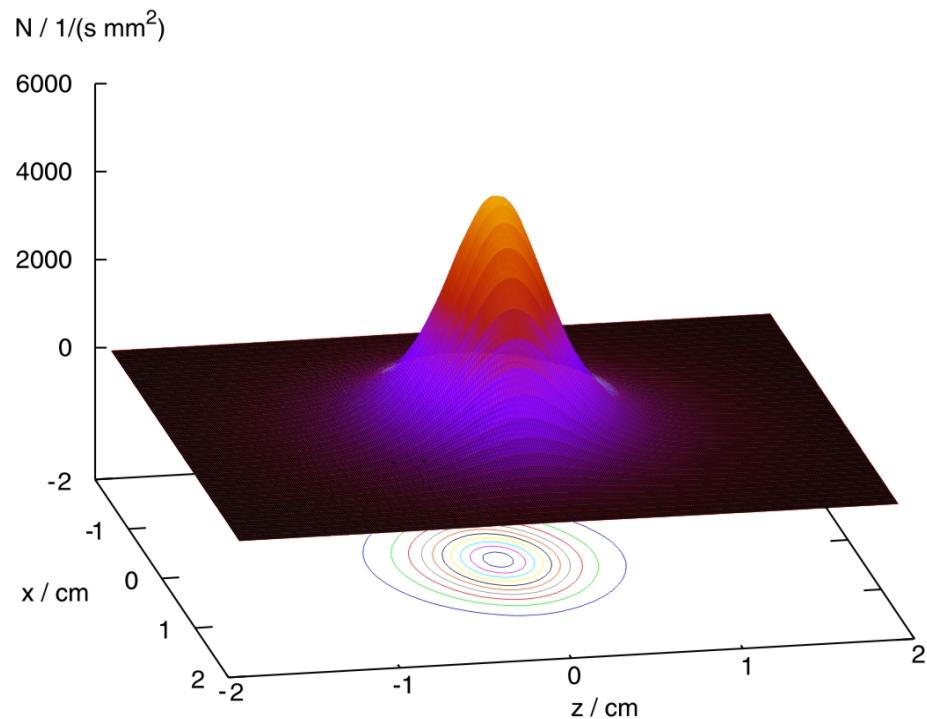
$$N(x_d, z_d) = \int_{S_0}^{S_1} ds \int_{Z_0}^{Z_1} dz \int_{X_0}^{X_1} dx \int_{Z'_0}^{Z'_1} dz' \int_{X'_0}^{X'_1} dx' \frac{d\sigma}{d\omega}(\vartheta, \phi) \sin(\vartheta) \frac{\partial(\vartheta, \phi)}{\partial(x, z)} \cdot \rho_e(x, z, x', z', s) \cdot \rho(x, z, s)$$



Simulation of the Compton Process

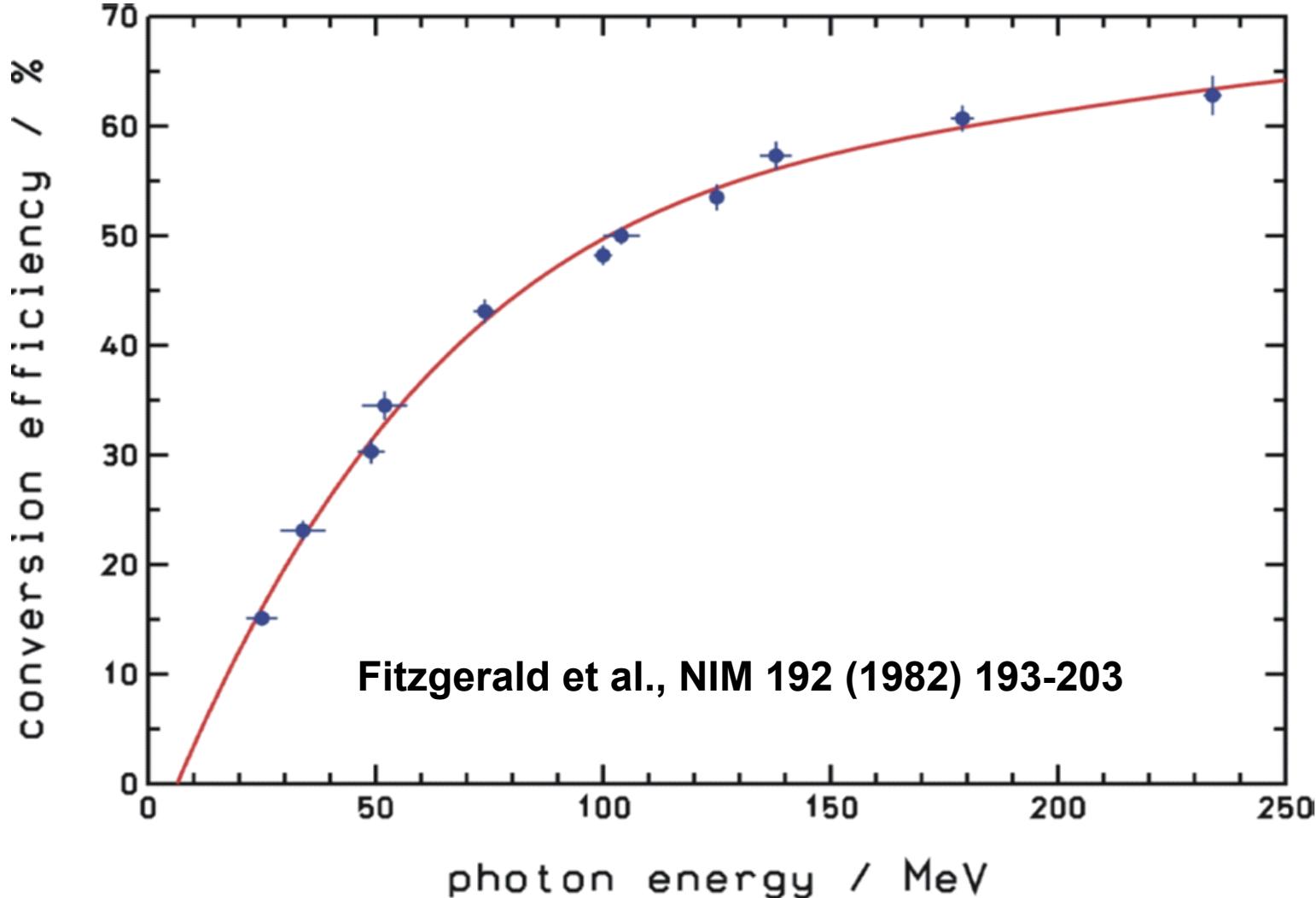
Distribution of the backscattered photons

Rate asymmetry

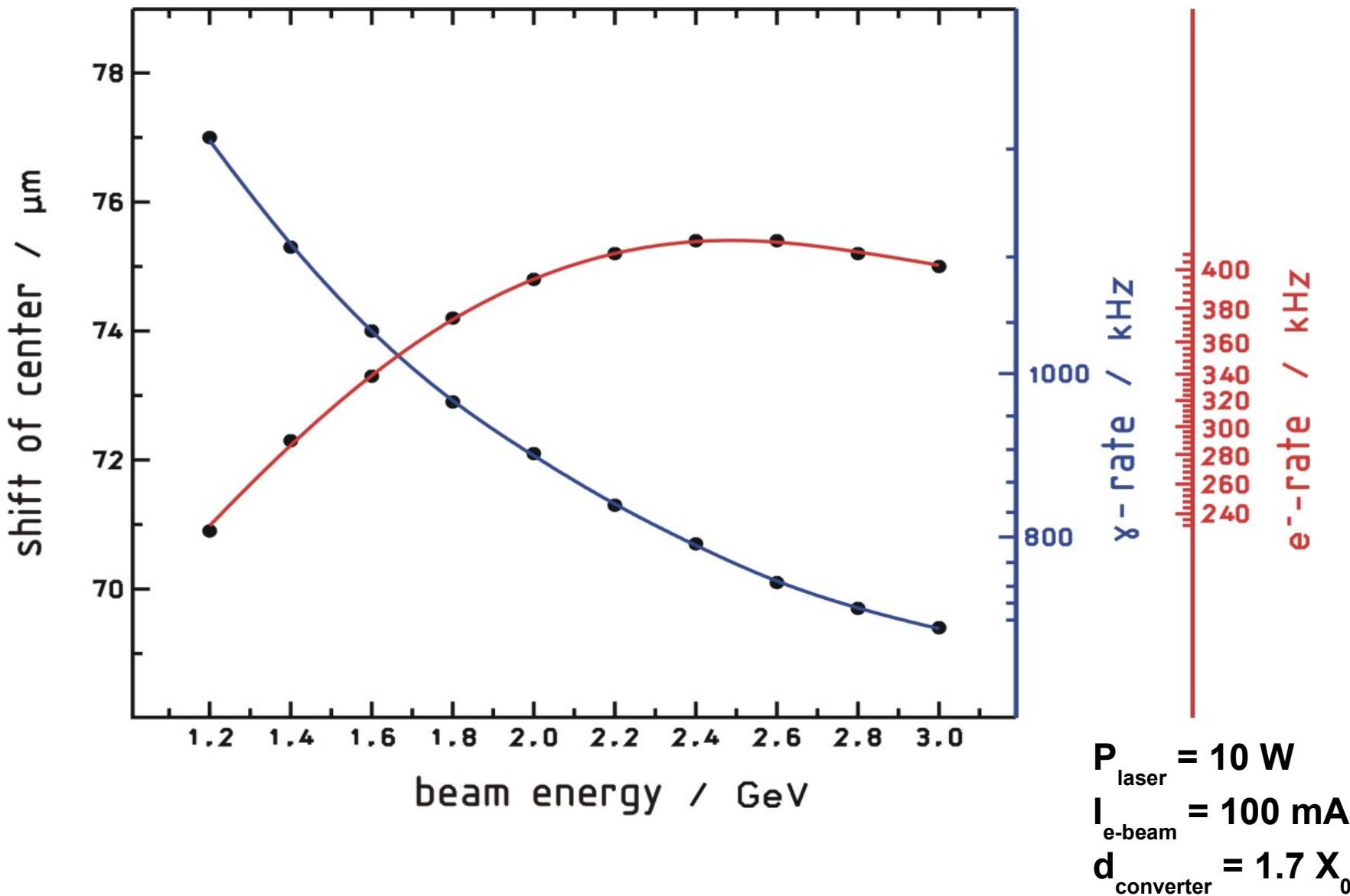


Simulation of the Compton Process

e^+/e^- pair conversion ; $d=1.7 X_0$

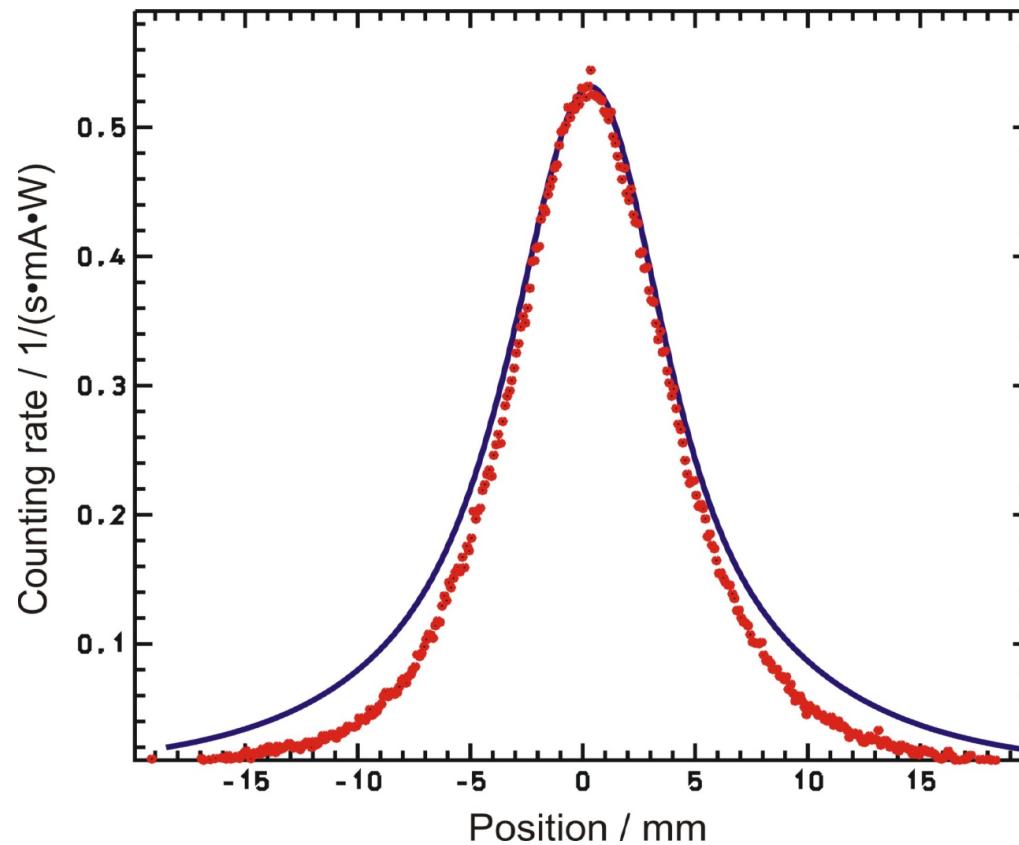


Analyzing Power

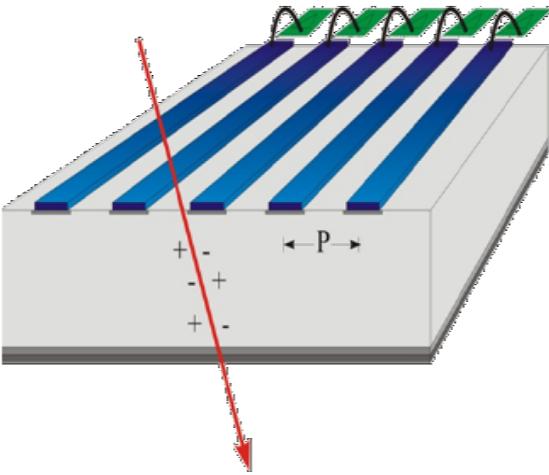


Simulation of the Compton Process

Comparison between simulation and a real measurement with a previous prototype detector



Required Pitch

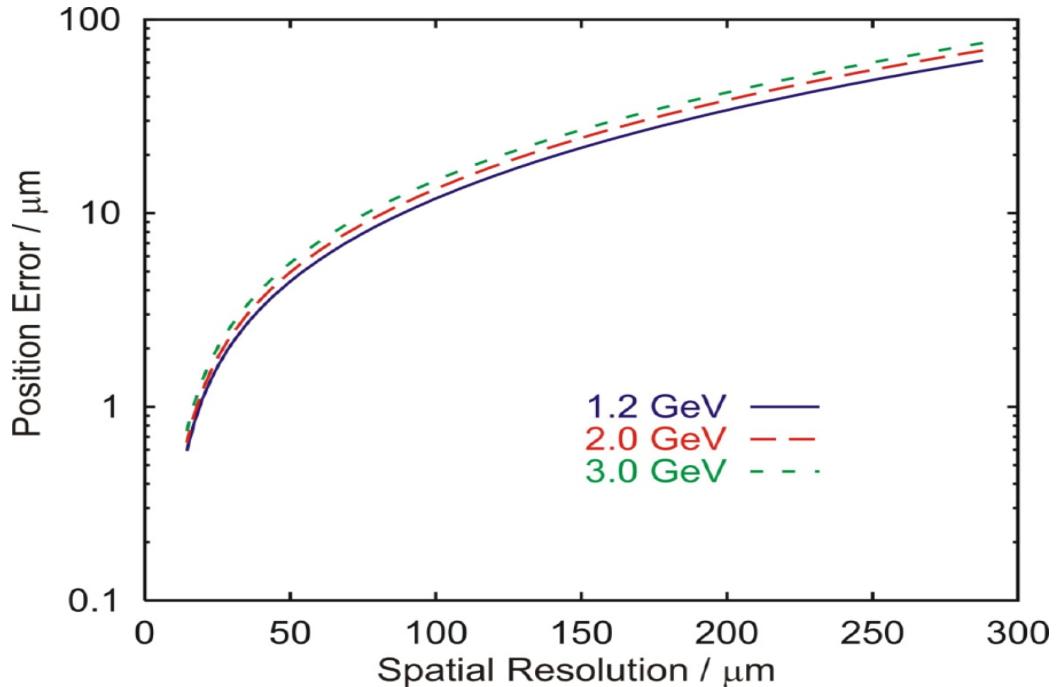


spatial resolution:

$$\Delta z_{det} = \frac{p}{\sqrt{12}}$$

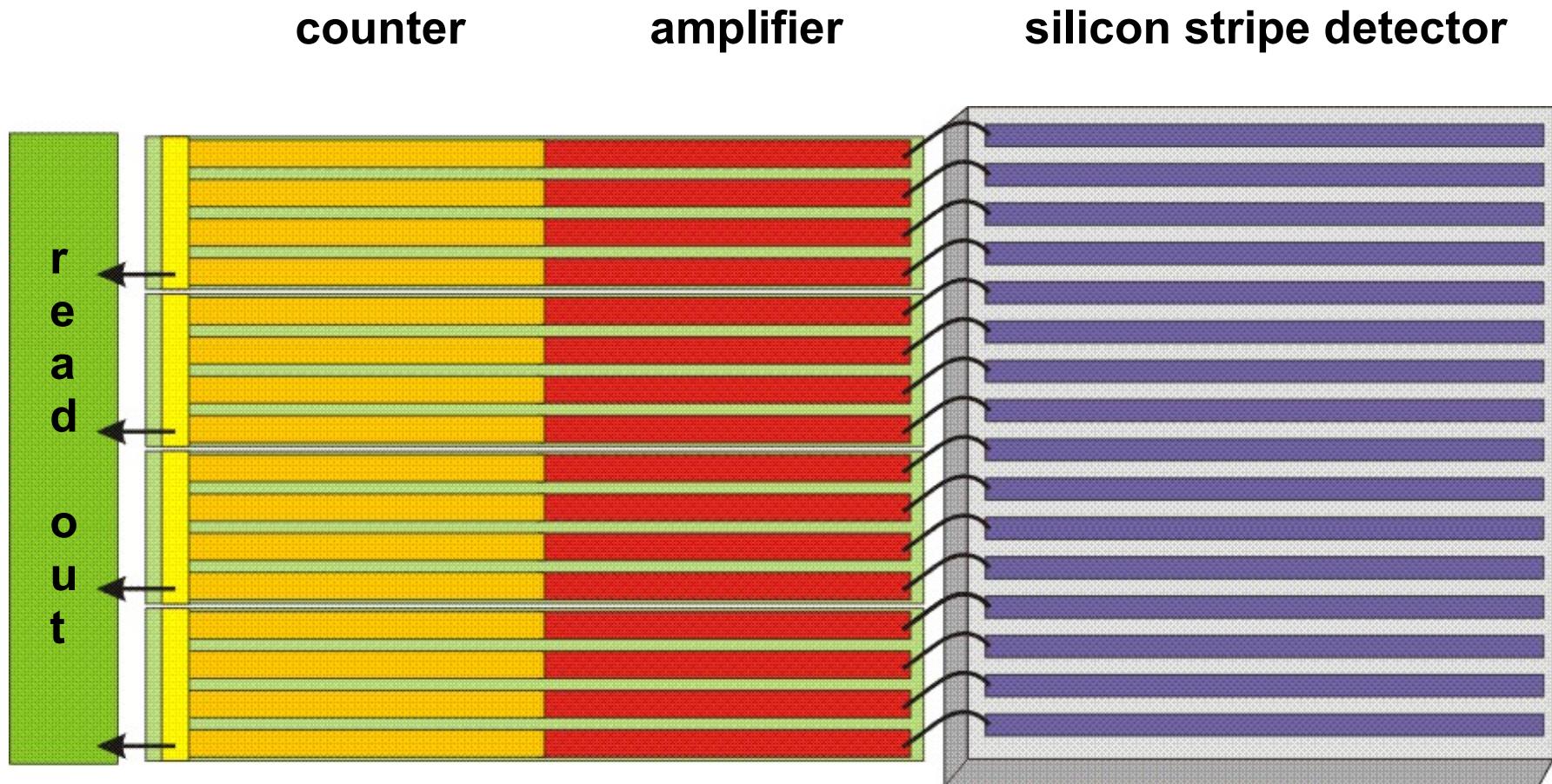
achievable position error:

$$\Delta \bar{z} = \sqrt{\frac{\sigma_z^2}{N^2} + \frac{\sum n_i^2}{N^2} \cdot \Delta z_{det}^2}$$

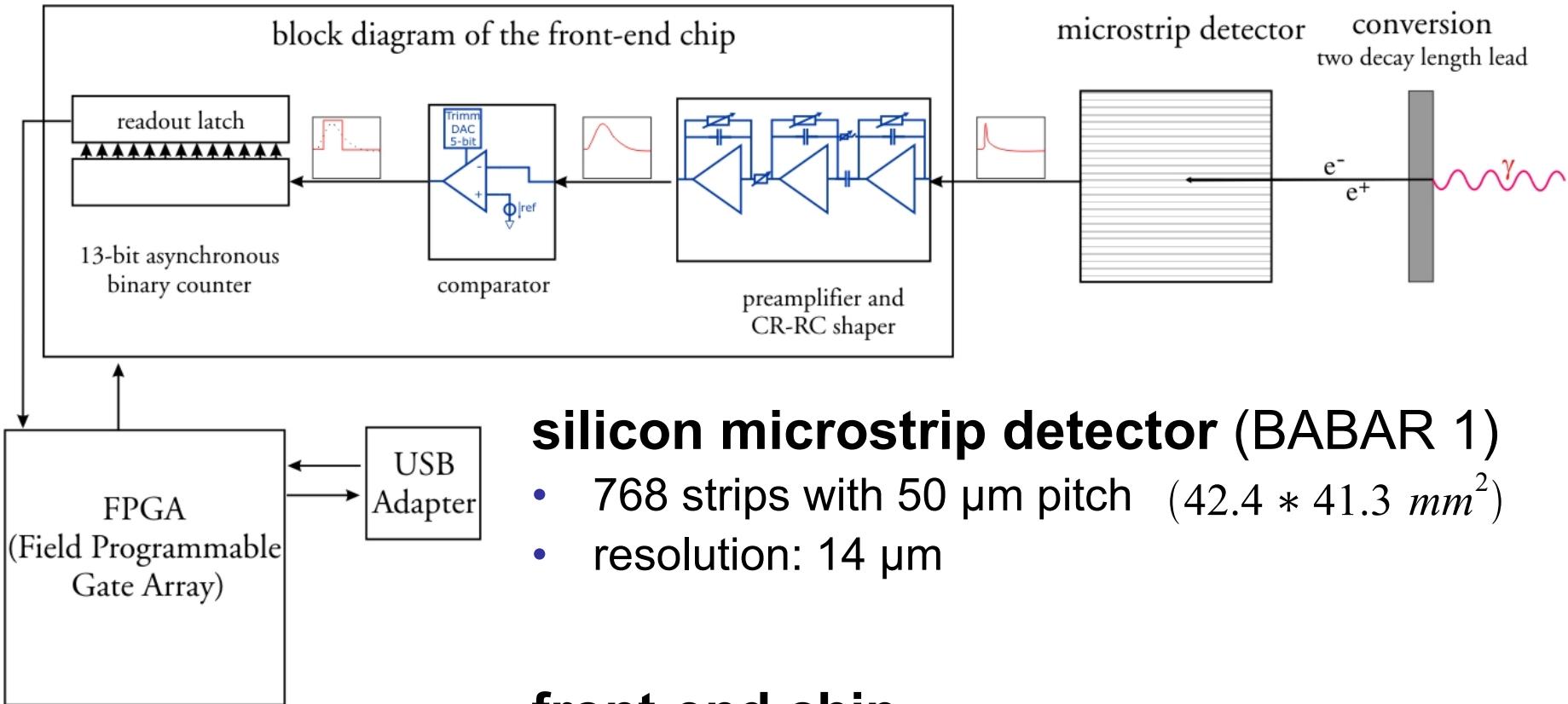


$$\Delta P \leq 1^0 /_0 \longleftrightarrow \Delta z \leq 0.7 \mu\text{m} \longleftrightarrow p \approx 50 \mu\text{m}$$

Detector Design



Detector Design



silicon microstrip detector (BABAR 1)

- 768 strips with $50 \mu\text{m}$ pitch ($42.4 * 41.3 \text{ mm}^2$)
- resolution: $14 \mu\text{m}$

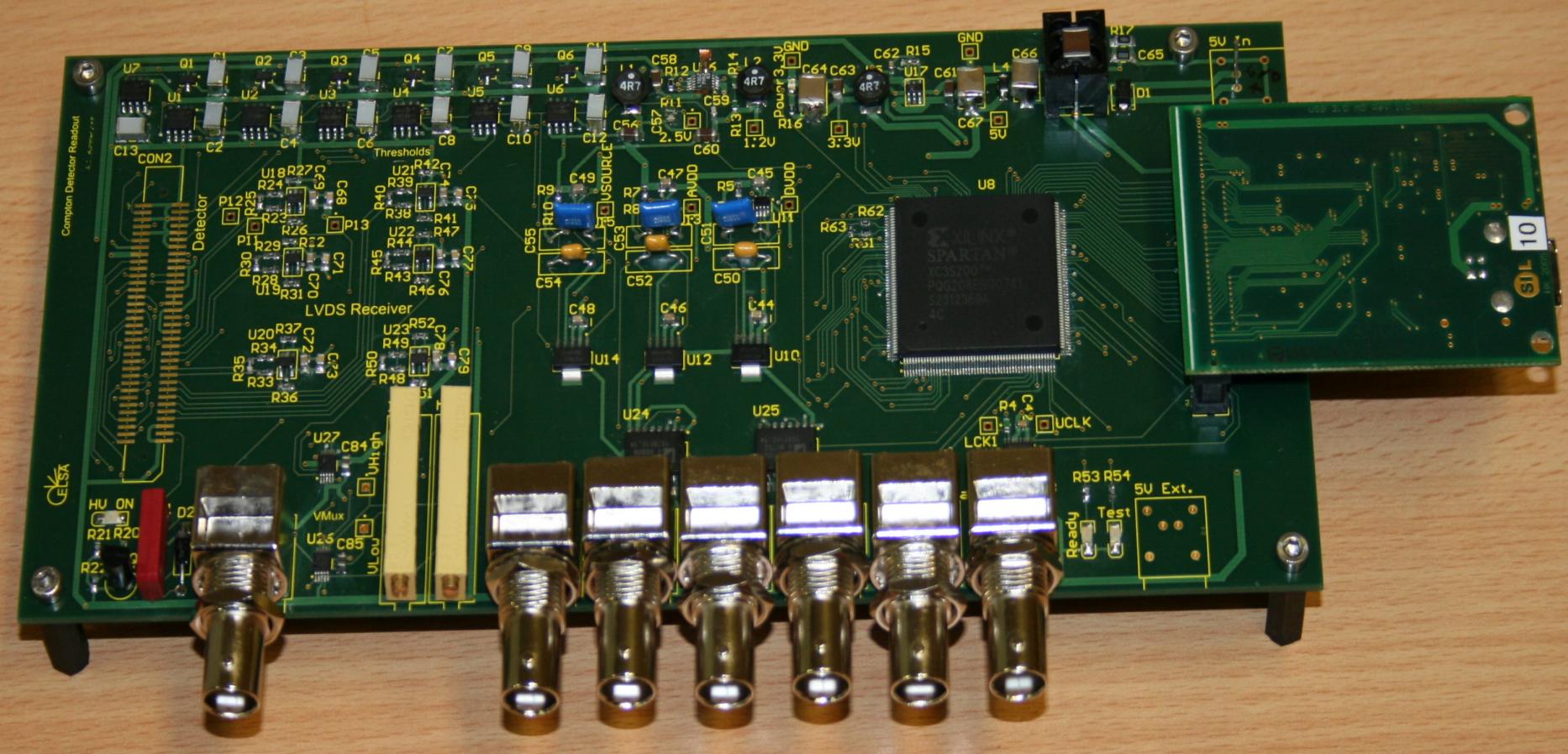
front-end chip

- high rate acceptance (10 - 150 MHz)
- digital part build in LVDS technology
- internal logic controls the readout process

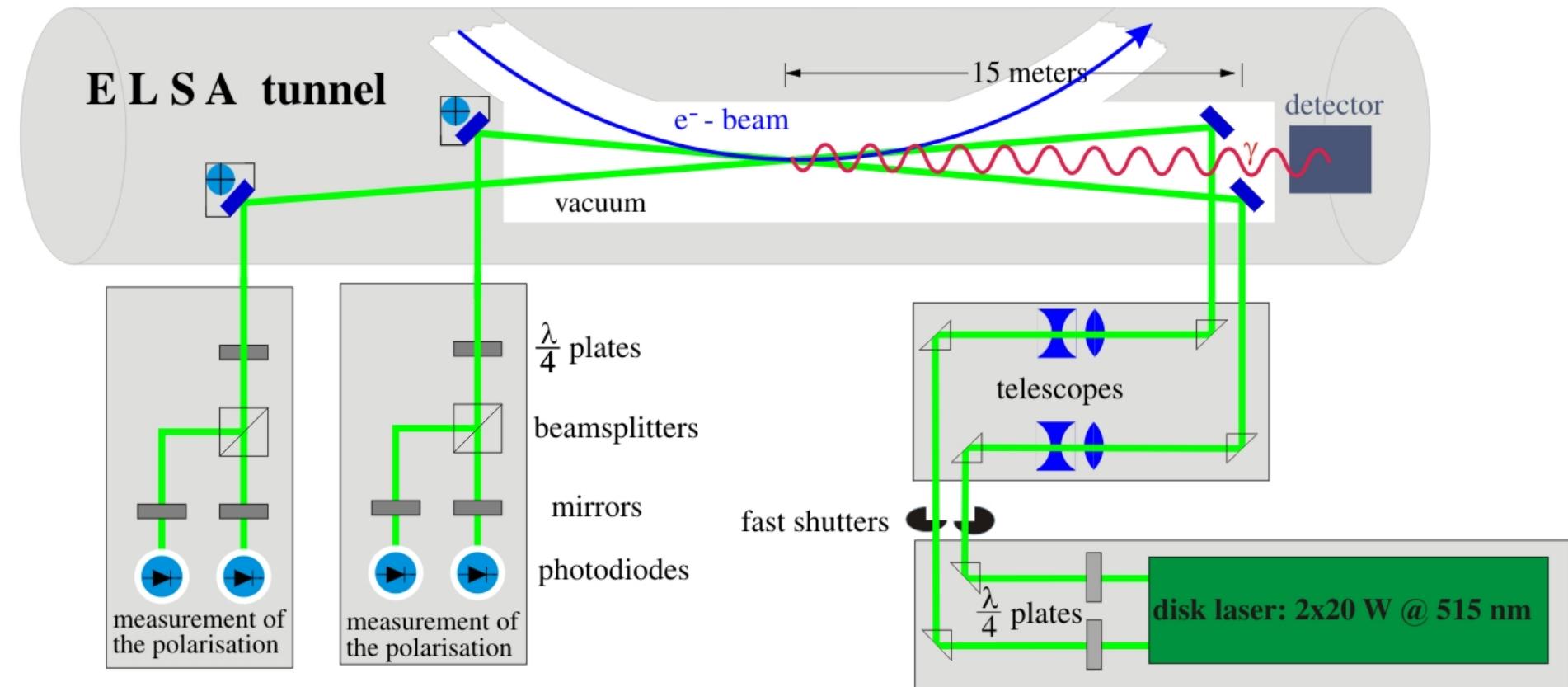
Detector Design

Measurement program:

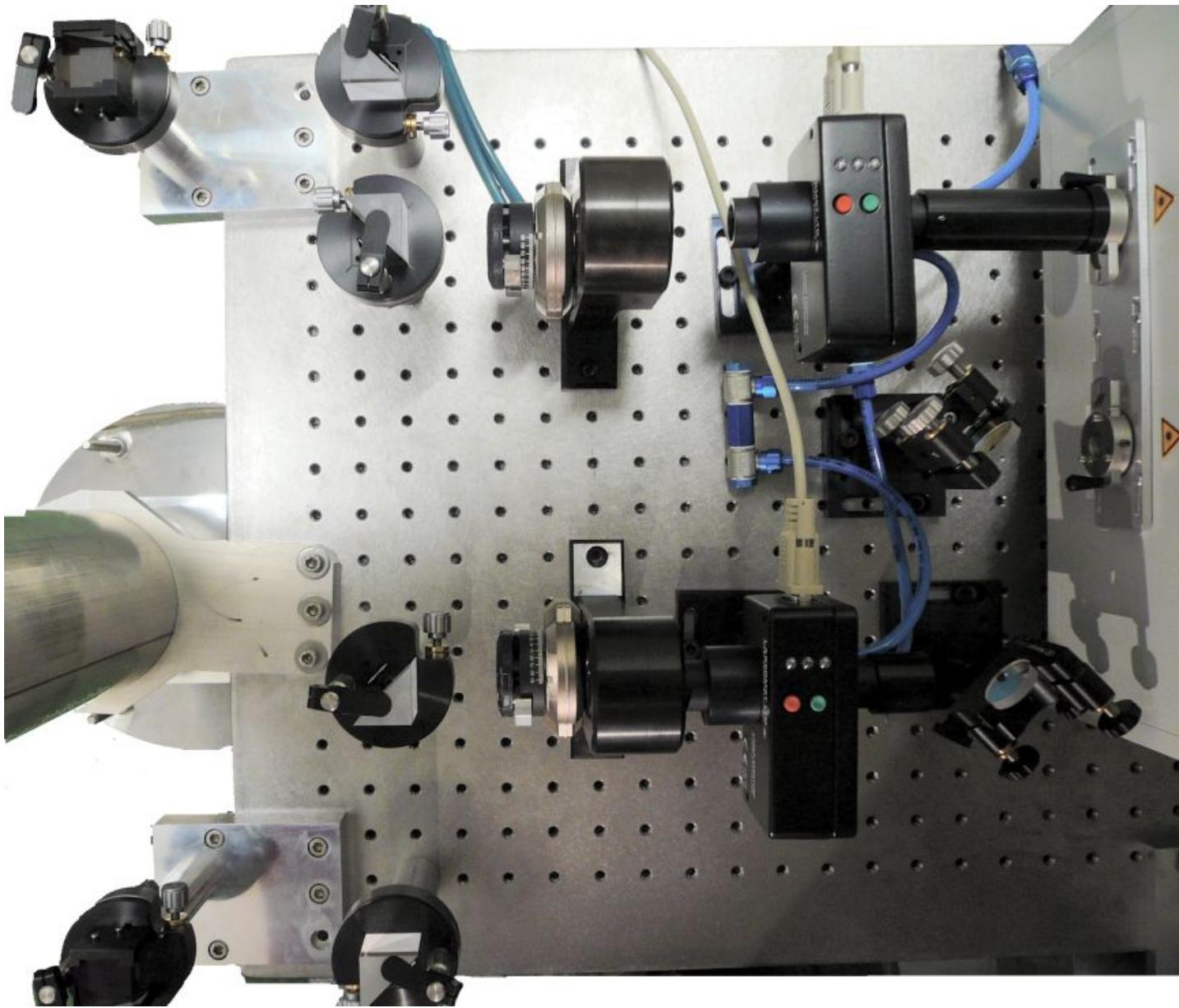
- $S_3 = 1$
- background
- $S_3 = -1$
- $S_3 = -1$
- background
- $S_3 = 1$



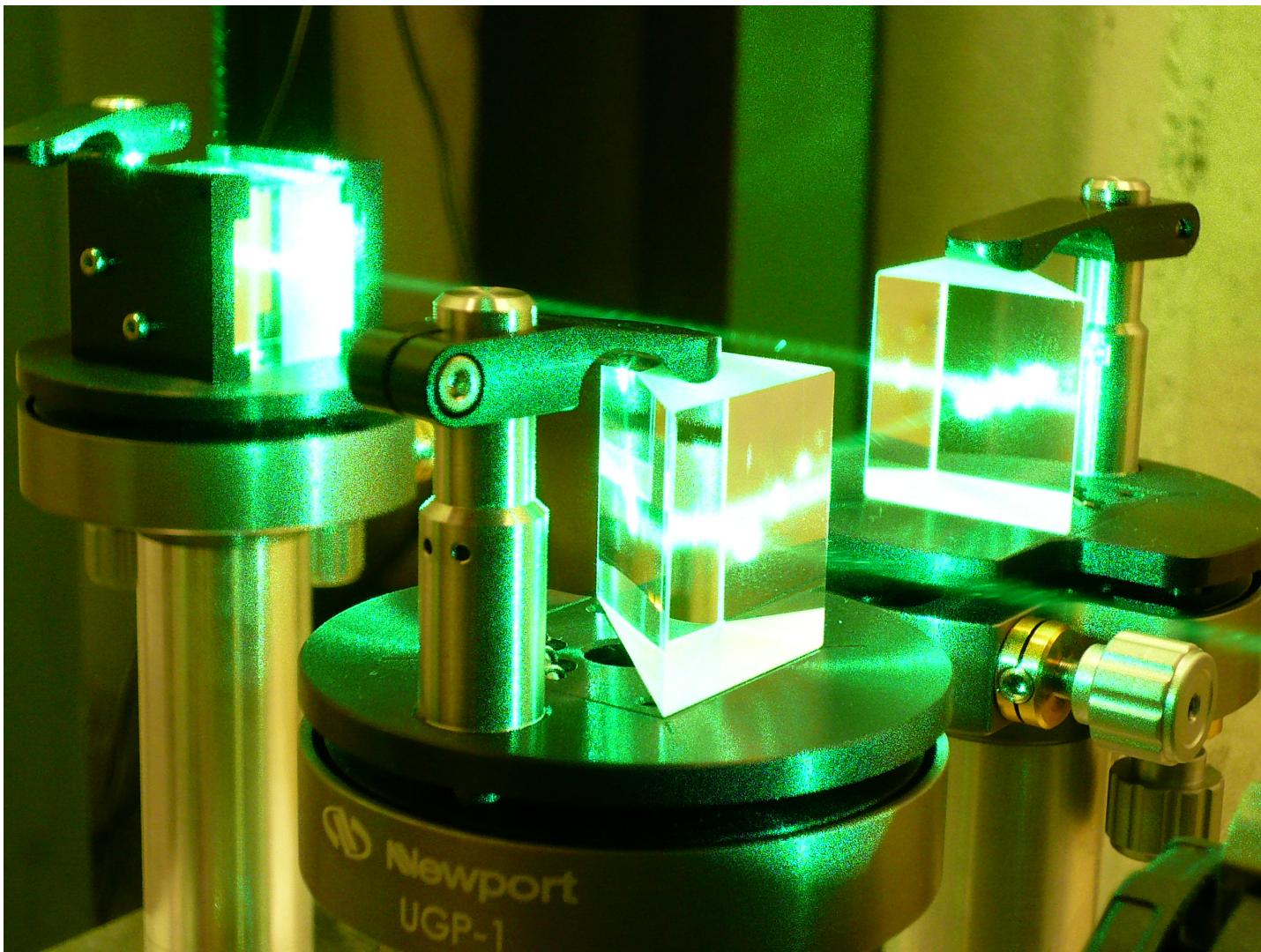
Laser Beam Line



Laser Beam Line



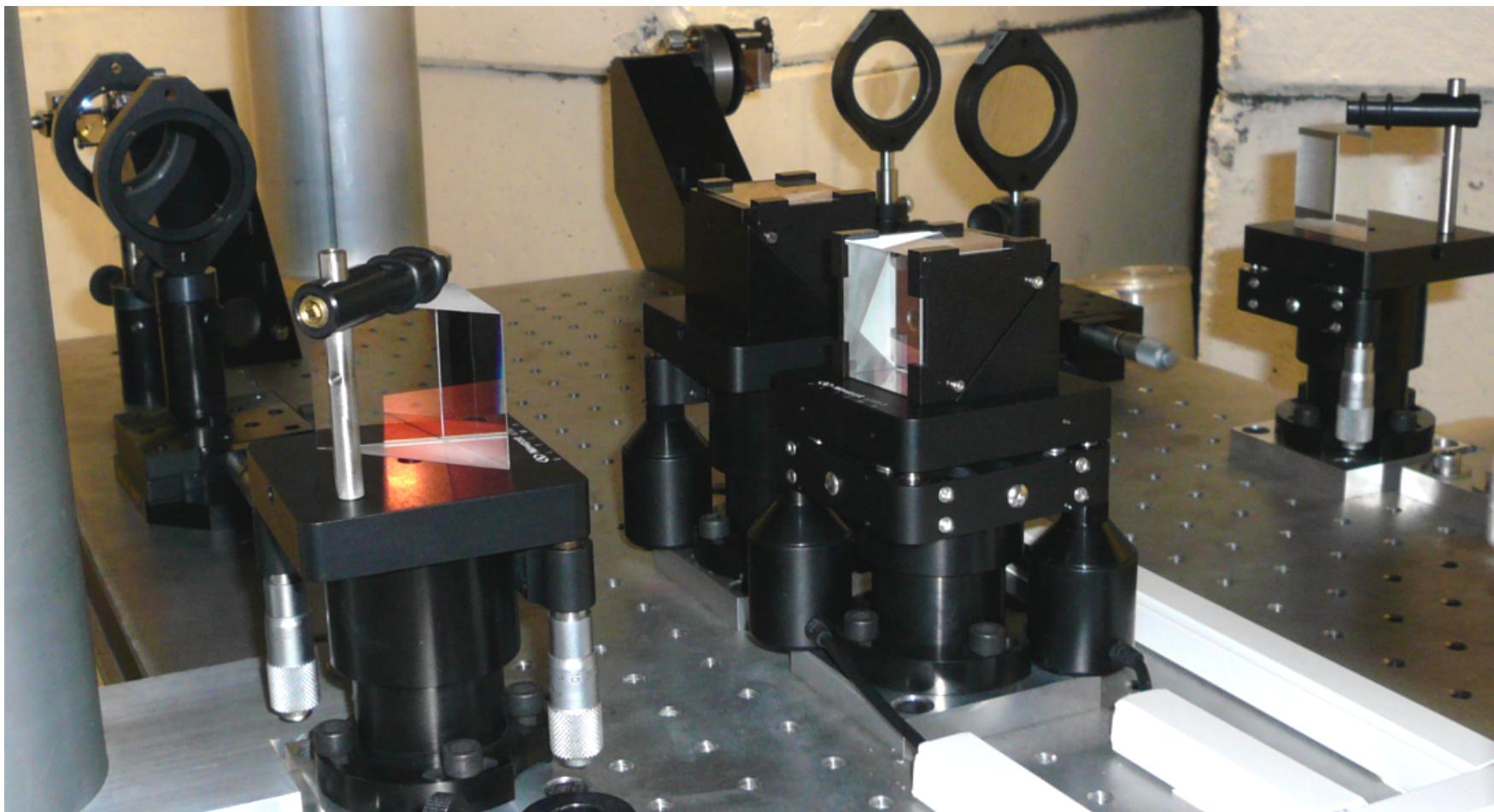
Laser Beam Line



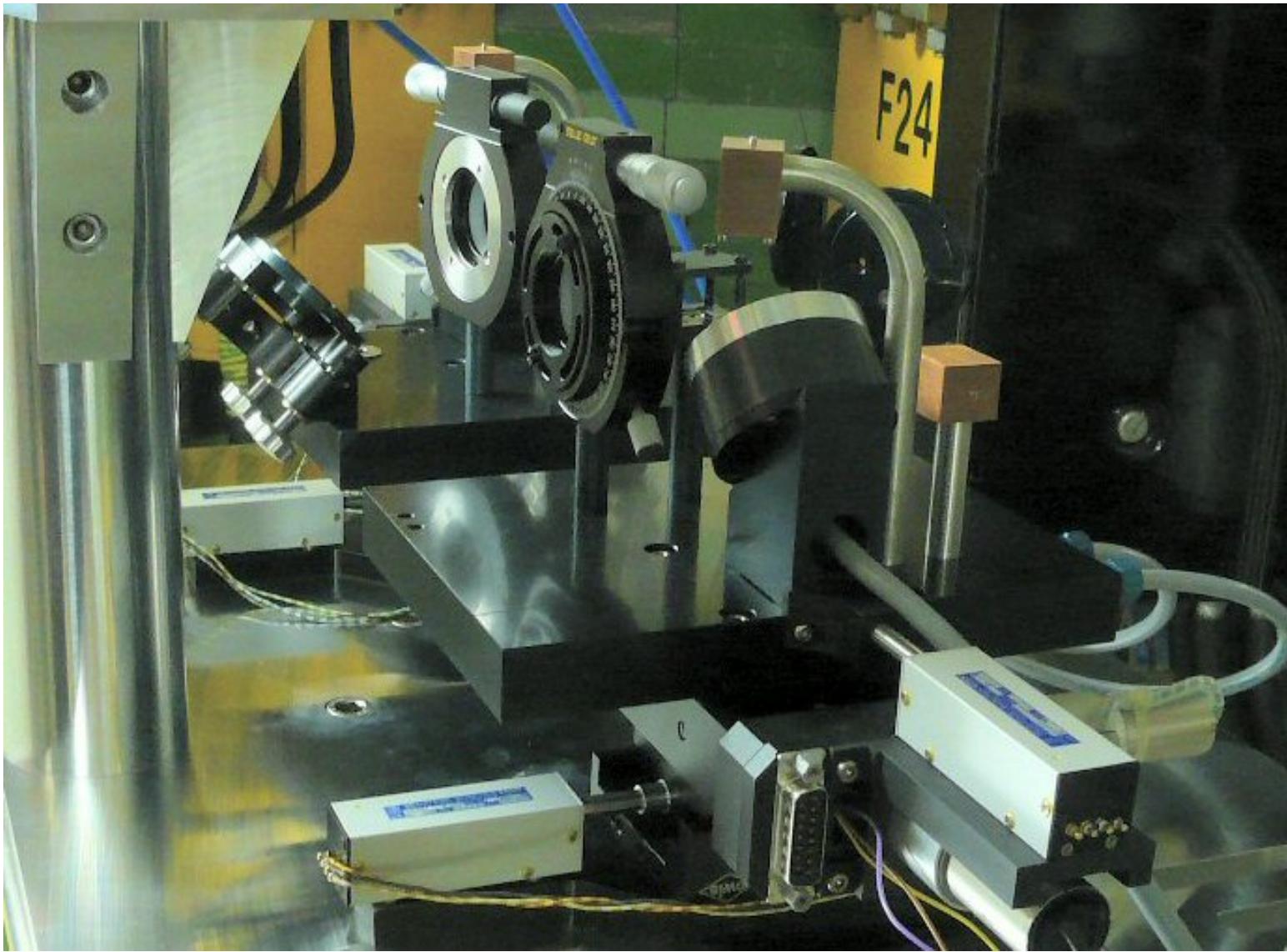
Laser Beam Line



Laser Beam Line

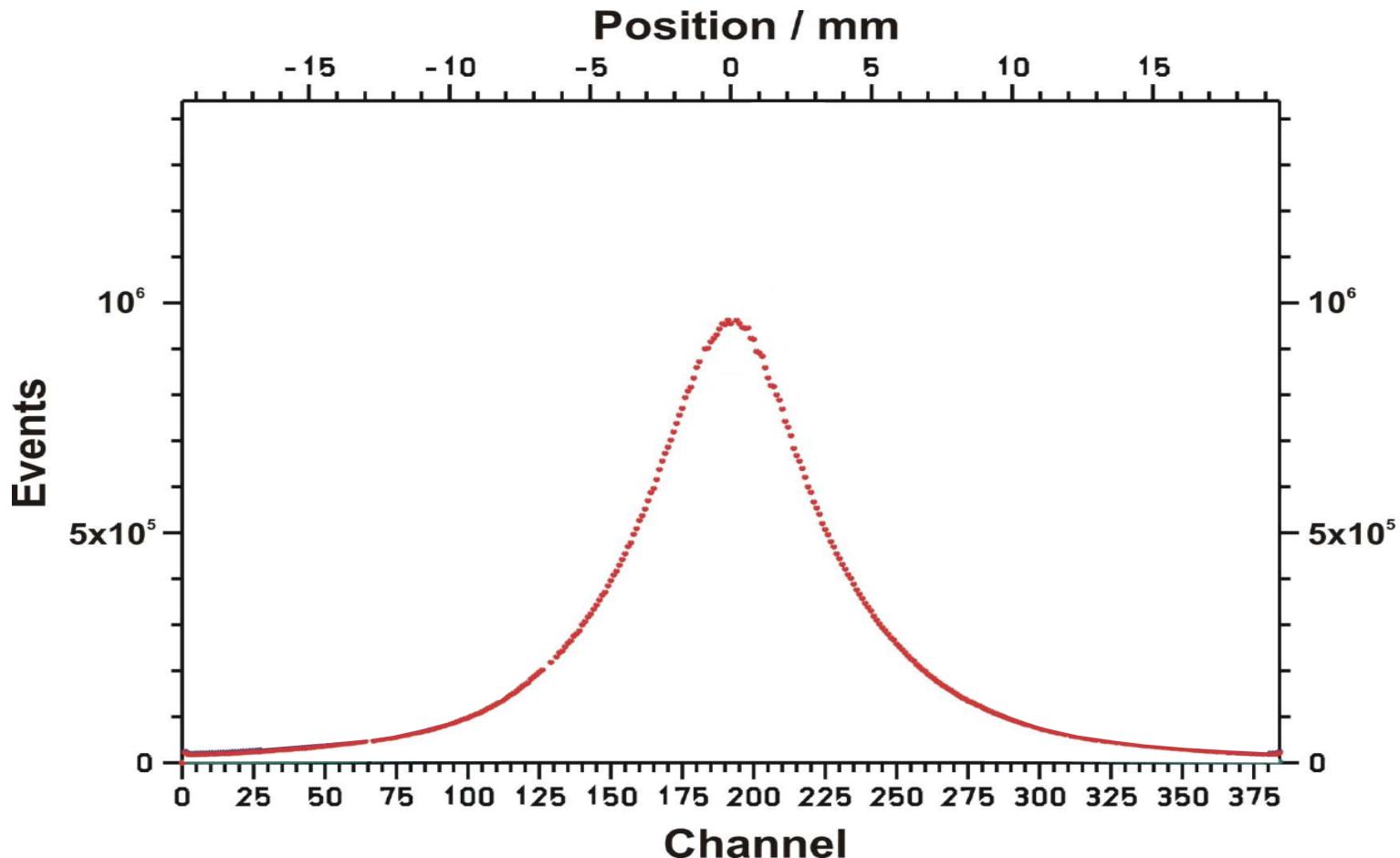


Laser Beam Line



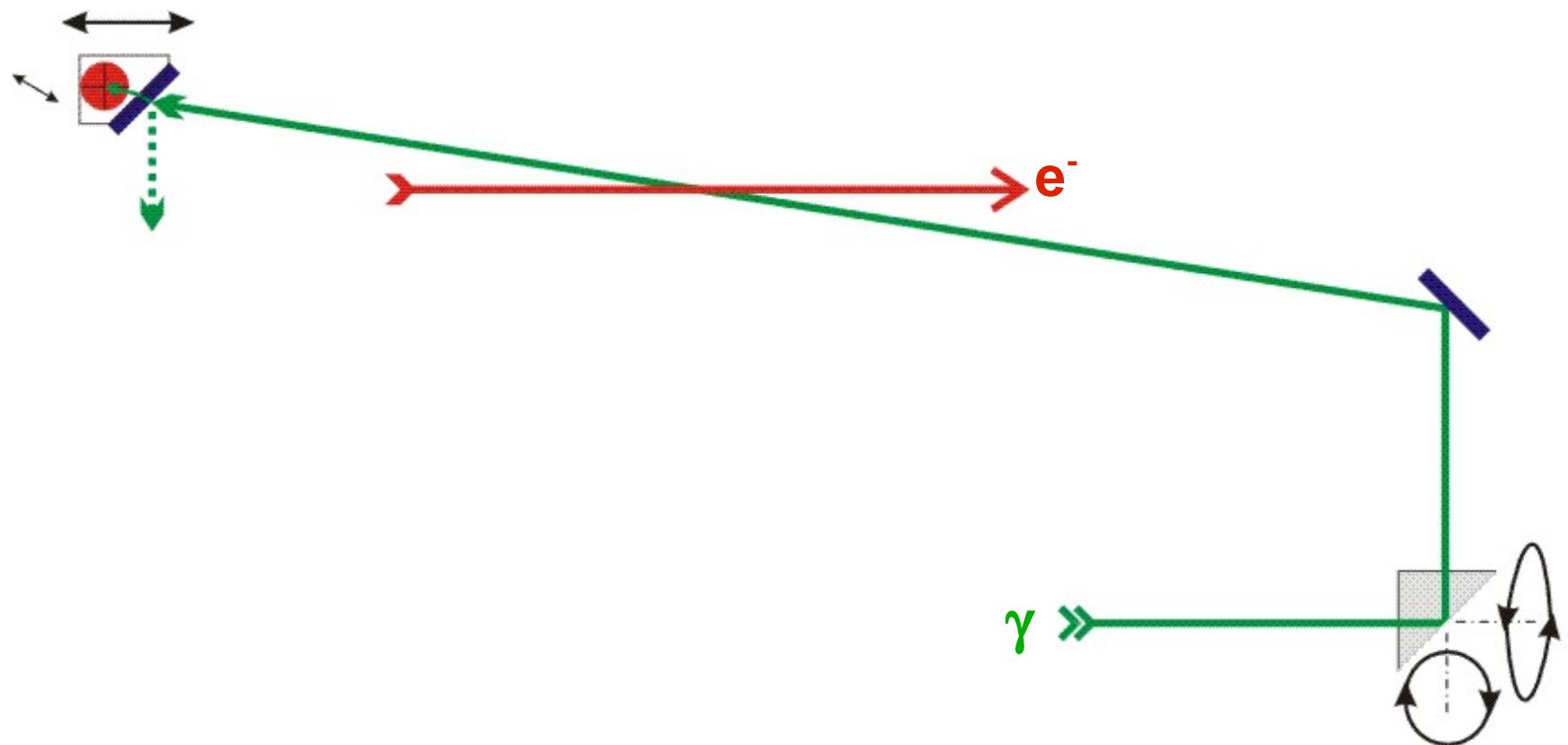
Beamdiagnostics

- Measurement without laser beam delivers profile of convolution of the e^- beam width and divergence



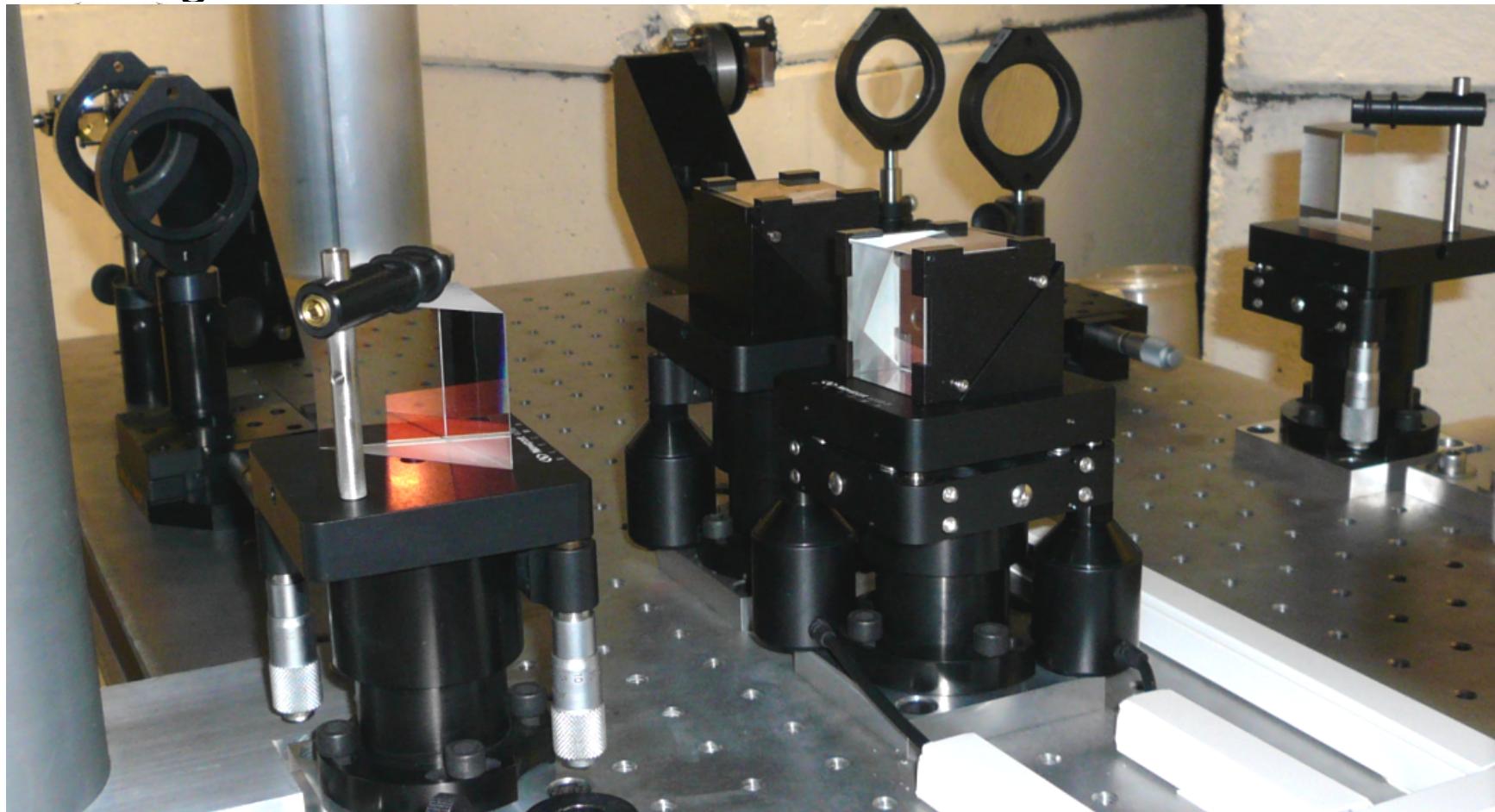
Beamdiagnostics

Scanning of the horizontal e^- beam width



Beamdiagnostics

Scanning of the horizontal e^- beam width



Outlook

- First detector tests this year with a smaller detector
- Complete detector and laser setup in spring next year
- In the future the capabilities as a beamdiagnosis element will be investigated